

Description

The SX15N10D uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 100V$ $I_D = 19.3A$

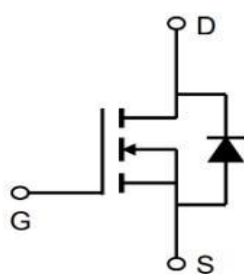
$R_{DS(ON)} < 85m\Omega$ @ $V_{GS}=10V$

Application

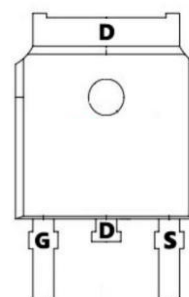
Lithium battery protection

Wireless impact

Mobile phone fast charging



TO-252-3L



Absolute Maximum Ratings (TC=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_C=25^\circ C$	Drain Current, $V_{GS} @ 10V$	19.3	A
$I_D @ T_C=100^\circ C$	Drain Current, $V_{GS} @ 10V$	10	A
IDM	Pulsed Drain Current ¹	57.9	A
$P_D @ T_C=25^\circ C$	Total Power Dissipation	30	W
$P_D @ T_A=25^\circ C$	Total Power Dissipation ³	2.7	W
EAS	Single Pulse Avalanche Energy ⁴	7	mJ
TSTG	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C
$R_{\theta JA}$	Maximum Thermal Resistance, Junction-ambient	55	°C/W
$R_{\theta JC}$	Maximum Thermal Resistance, Junction-case	5.1	°C/W

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
V(BR)DSS	Drain-Source Breakdown Voltage	VGS=0V, ID=250μA	100	107	-	V
IDSS	Zero Gate Voltage Drain Current	VDS=100V, VGS=0V,	-	-	1.0	μA
IGSS	Gate to Body Leakage Current	VDS=0V, VGS=±20V	-	-	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS, ID=250μA	1.2	1.85	2.5	V
RDS(on)	Static Drain-Source on-Resistance note3	VGS=10V, ID=5A	-	65	85	mΩ
		VGS=4.5V, ID=3A	-	75	100	mΩ
g fs	Forward Transconductance	V DS =5V , I D =5A		14		S
RG	Gate Resistance	VDS = 0V, VGS =0V,f =1MHz		3		Ω
Ciss	Input Capacitance	VDS=15V, VGS=0V, f=1.0MHz	-	1100	-	pF
Coss	Output Capacitance		-	55	-	pF
Crss	Reverse Transfer Capacitance		-	40	-	pF
Qg	Total Gate Charge	VDS=50V, ID=5A, VGS=10V	-	11.9	-	nC
Qgs	Gate-Source Charge		-	2.8	-	nC
Qgd	Gate-Drain("Miller") Charge		-	1.7	-	nC
td(on)	Turn-on Delay Time	VDS=30V, ID=5A, RG=1.8Ω, VGS=10V	-	3.8	-	ns
tr	Turn-on Rise Time		-	25.8	-	ns
td(off)	Turn-off Delay Time		-	16	-	ns
tf	Turn-off Fall Time		-	8.8	-	ns
IS	Continuous Source Current1,5	VG=VD=0V , Force Current	-	-	14.6	A
ISM	Pulsed Source Current2,5		-	-	25	A
VSD	Diode Forward Voltage2	VGS=0V, IS=10A	-	-	1.2	V

Notes:

1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.

2、The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%

3、The EAS data shows Max. rating . The test condition is VDD =80V,VGS =10V,L=0.1mH,I AS =7A

4、The power dissipation is limited by 150°Cjunction temperature

5、The data is theoretically the same as I D and I DM , in real applications , should be limited by total power dissipation

Typical Characteristics

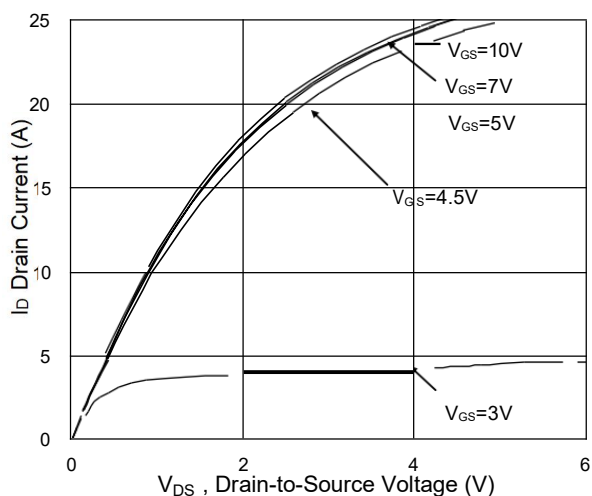


Fig.1 Typical Output Characteristics

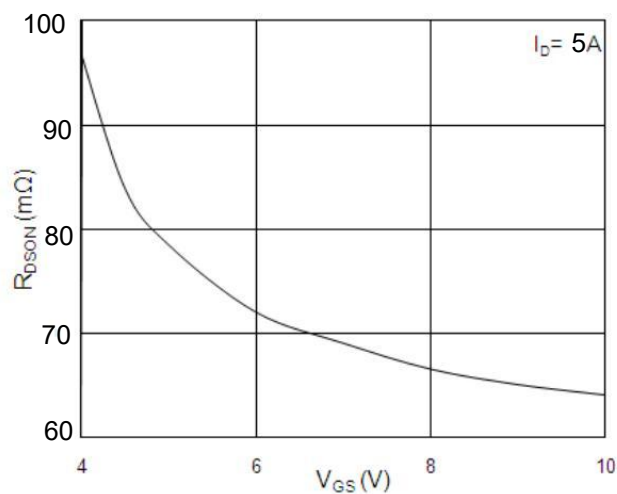


Fig.2 On-Resistance vs. Gate-Source

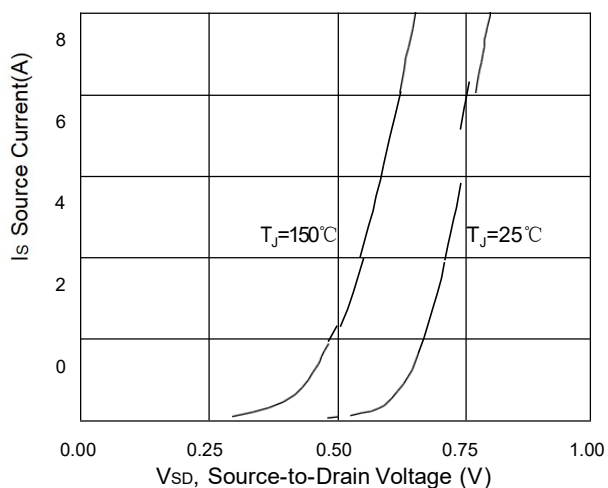


Fig.3 Forward Characteristics Of Reverse

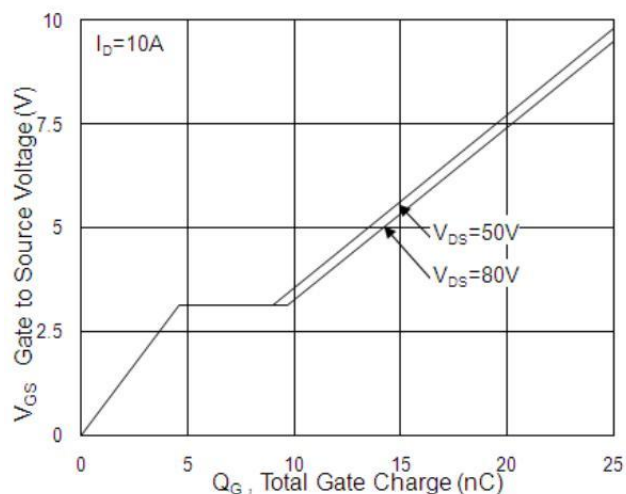


Fig.4 Gate-Charge Characteristics

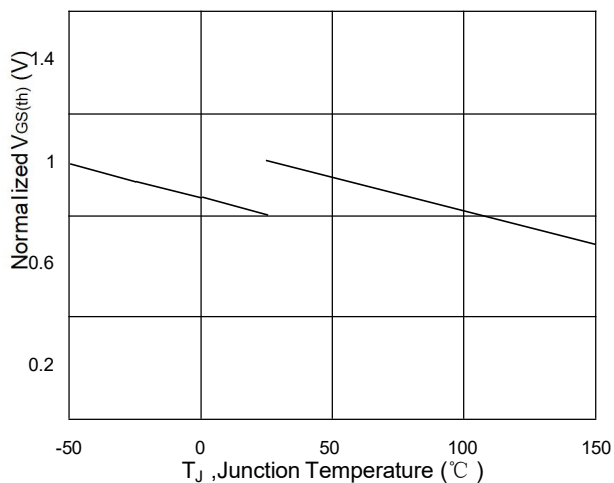


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

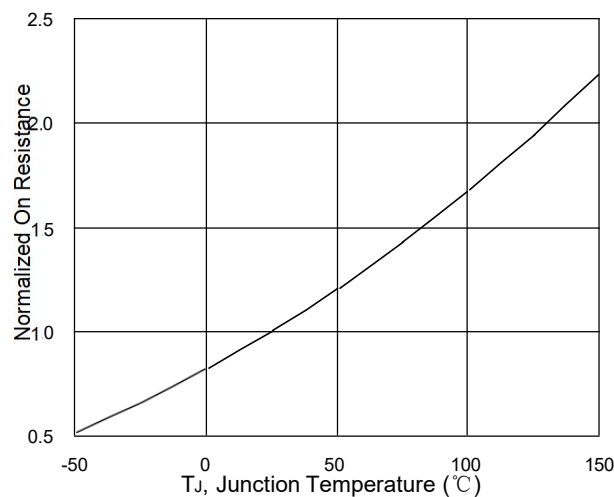
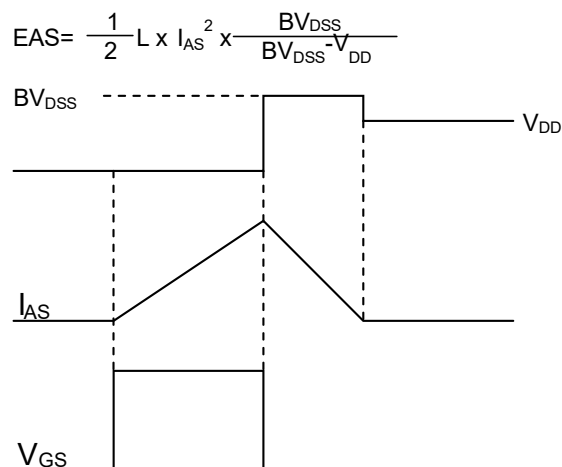
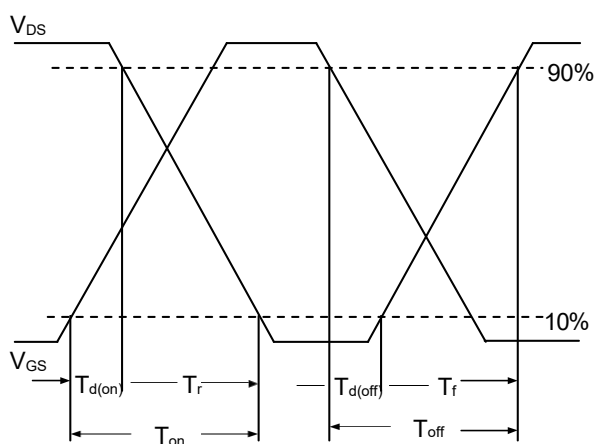
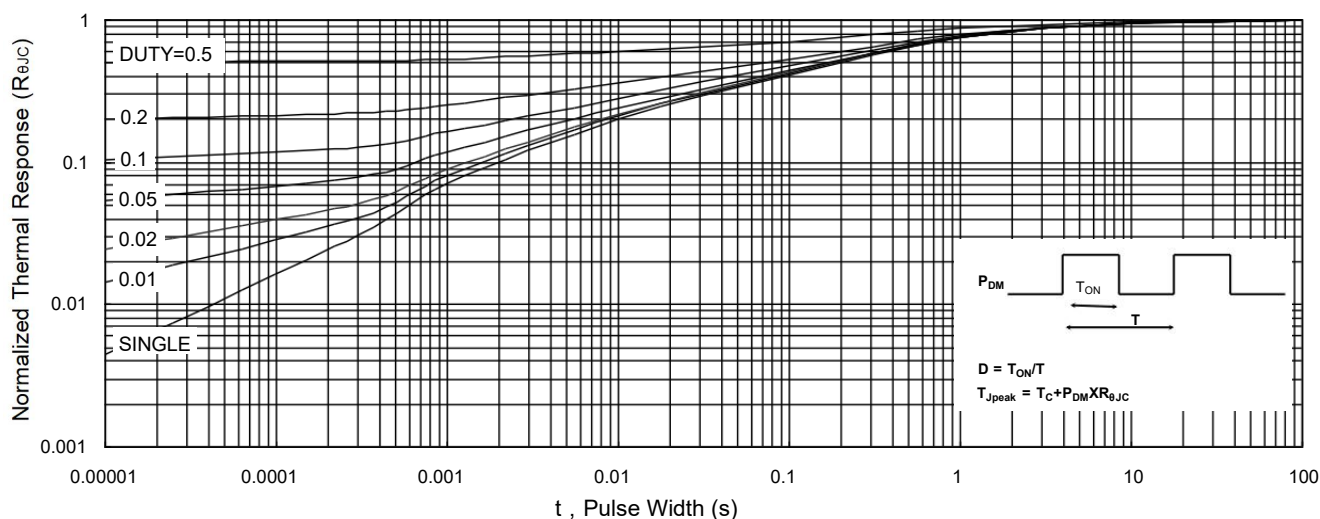
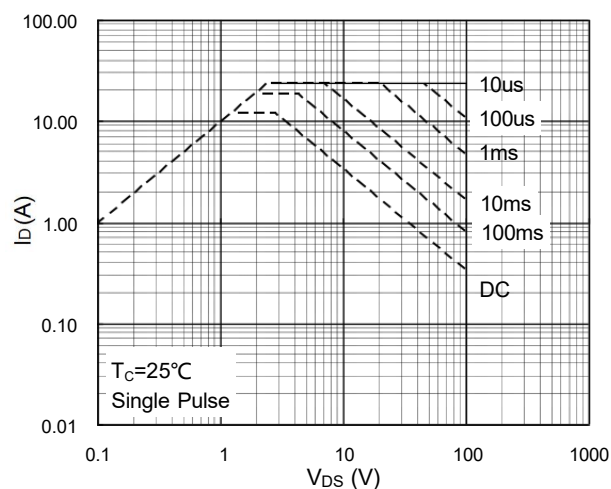
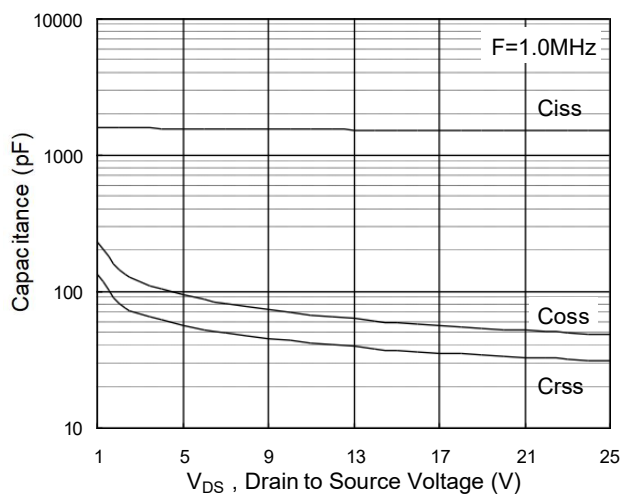


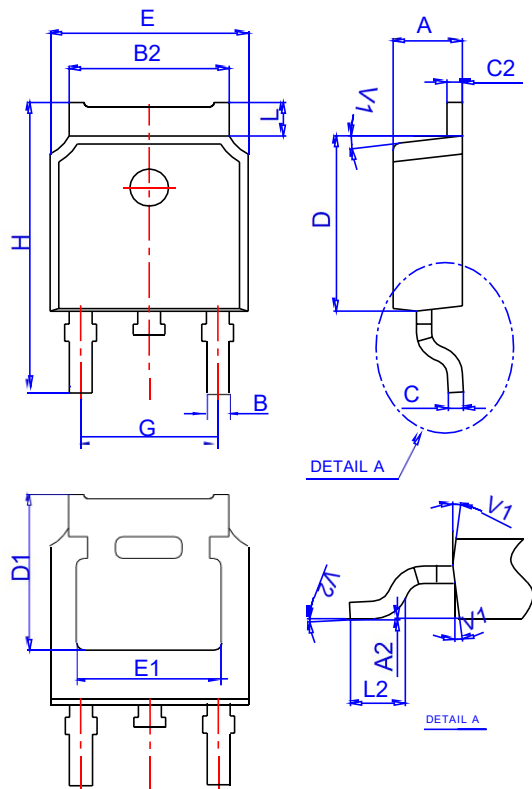
Fig.6 Normalized $R_{DS(on)}$ vs. T_J

Typical Characteristics



$$EAS = \frac{1}{2} L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$

Package Mechanical Data : TO-252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	TO-252-3L		2500